

Title (en)
RADIATION-EMITTING OPTOELECTRONIC COMPONENT

Title (de)
STRAHLUNGSEMITTIERENDES OPTOELEKTRONISCHES BAUELEMENT

Title (fr)
COMPOSANT OPTOELECTRONIQUE EMETTANT UN RAYONNEMENT

Publication
EP 1929548 A1 20080611 (DE)

Application
EP 06791402 A 20060927

Priority

- DE 2006001701 W 20060927
- DE 102005046368 A 20050928
- DE 102005062514 A 20051227

Abstract (en)
[origin: DE102005062514A1] An opto-electronic component has a semiconductor (1) with an active semiconductor layer sequence (2) that converts electromagnetic radiation of a first wave length emitted by the front face (3) of the semiconductor. The semiconductor further incorporates a material (6) that converts emissions of the first wavelenth into a second wavelength. The chip has a selective reflecting layer (8) located between the active semiconductor layered sequence (2) and the first wavelength conversion substance (6). The reflector allows passage of the first wavelength and reflects the second.

IPC 8 full level
H01L 33/46 (2010.01); **H01L 33/50** (2010.01)

CPC (source: EP US)
H01L 33/46 (2013.01 - EP US); **H01L 33/50** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

C-Set (source: EP US)
H01L 2924/0002 + **H01L 2924/00**

Citation (search report)
See references of WO 2007036214A1

Citation (examination)

- DE 10261428 A1 20040722 - OSRAM OPTO SEMICONDUCTORS GMBH [DE]
- US 4634926 A 19870106 - VRIENS LEENDERT [NL], et al

Designated contracting state (EPC)
DE

DOCDB simple family (publication)
DE 102005062514 A1 20070329; CN 101297412 A 20081029; CN 101297412 B 20110406; EP 1929548 A1 20080611; JP 2009510744 A 20090312; KR 20080059607 A 20080630; TW 200717879 A 20070501; TW I334651 B 20101211; US 2009261366 A1 20091022; US 8598604 B2 20131203; WO 2007036214 A1 20070405

DOCDB simple family (application)
DE 102005062514 A 20051227; CN 200680040257 A 20060927; DE 2006001701 W 20060927; EP 06791402 A 20060927; JP 2008532593 A 20060927; KR 20087010160 A 20080428; TW 95135079 A 20060922; US 8825006 A 20060927